

I. Power section

Absolute maximum ratings		$T_s = 25^\circ\text{C}$ unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}	Operating DC link voltage	1700	V
$V_{CC}^{1)}$		1200	V
V_{GES}		± 20	V
I_C	$T_s = 25 (70)^\circ\text{C}$	1800 (1350)	A
Inverse diode			
$I_F = -I_C$	$T_s = 25 (70)^\circ\text{C}$	1350 (1005)	A
I_{FSM}	$T_j = 150^\circ\text{C}$, $t_p = 10\text{ms}$; sin	12960	A
I^2t (Diode)	Diode, $T_j = 150^\circ\text{C}$, 10ms	840	kJ^2/s
$T_j, (T_{stg})$	rms, AC, 1min per AC terminal, rms, $T_s = 70^\circ\text{C}$, $T_{terminal} < 115^\circ\text{C}$	-40...+150 (125)	$^\circ\text{C}$
V_{isol}		4000	V
$I_{AC-terminal}$		400	A

Characteristics $T_s = 25^{\circ}\text{C}$ unless otherwise specified								
Symbol	Conditions	min.	typ.	max.	Units			
IGBT								
V_{CESat}	$I_C = 900\text{A}$, $T_j = 25\ (125)^{\circ}\text{C}$; measured at terminal	–	1,9 (2,2)	2,4	V			
V_{CEO}	$T_j = 25\ (125)^{\circ}\text{C}$; at terminal	–	1,0 (0,9)	1,2 (1,1)	V			
r_{CE}	$T_j = 25\ (125)^{\circ}\text{C}$; at terminal	–	1,0 (1,4)	1,3 (1,7)	$\text{m}\Omega$			
I_{CES}	$V_{\text{GE}}=0$, $V_{\text{CE}}=V_{\text{CES}}$, $T_j=25(125)^{\circ}\text{C}$	–	3,6 (216)	–	mA			
$E_{\text{on}} + E_{\text{off}}$	$I_C=900\text{A}$, $V_{\text{CC}}=900\text{V}$	–	726	–	mJ			
	$T_j=125^{\circ}\text{C}$, $V_{\text{CC}}=1200\text{V}$	–	1071	–	mJ			
L_{CE}	top, bottom	–	4	–	nH			
C_{CHC}	per phase , AC side	–	3,0	–	nF			
$R_{\text{CC''-EE''}}$	terminal-chip, $T_j=25^{\circ}\text{C}$	–	0,17	–	$\text{m}\Omega$			
Inverse diode								
$V_F = V_{\text{EC}}$	$I_F = 900\text{A}$; $T_j = 25(125)^{\circ}\text{C}$ measured at terminal	–	1,6 (1,5)	2,0	V			
V_{TO}	$T_j = 25\ (125)^{\circ}\text{C}$	–	1,1 (0,8)	1,3 (1,0)	V			
r_T	$T_j = 25\ (125)^{\circ}\text{C}$	–	0,6 (0,8)	0,8 (1,0)	$\text{m}\Omega$			
E_{RR}	$I_C=900\text{A}$, $V_{\text{CC}}=900\text{V}$	–	129	–	mJ			
	$T_j=125^{\circ}\text{C}$, $V_{\text{CC}}=1200\text{V}$	–	153	–	mJ			
Mechanical data								
M_{dc}	DC terminals, SI Units	6	–	8	Nm			
M_{ac}	AC terminals, SI Units	13	–	15	Nm			
w	SKiiP® 3 System w/o heat sink	–	2,4	–	kg			
w	heat sink	–	5,2	–	kg			
Thermal characteristics (NWK 40; 8l/min; 50%glyc.); "s" reference to heat sink; "r" reference to built-in temperature sensor (acc. IEC 60747-15)								
R_{thjsIGBT}	per IGBT	–	–	0,017	$^{\circ}\text{C}/\text{W}$			
$R_{\text{thjsdiode}}$	per diode	–	–	0,033	$^{\circ}\text{C}/\text{W}$			
Z_{th}	R_i (mK/W) (max. values)				$\tau_{\text{au}}(\text{s})$			
	1	2	3	4	1	2	3	4
IGBT_{jr}	1,4	6,8	7,8	0,0	69,0	0,35	0,02	1,0
	2,6	4,0	17,7	17,7	50,0	5,0	0,25	0,04
diode_{jr}	4,6	4,7	1,1	0,6	48	15	2,8	0,4
$\text{heatsink}_{\text{ra}}$								

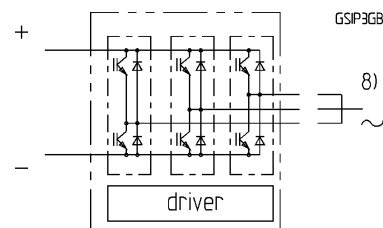
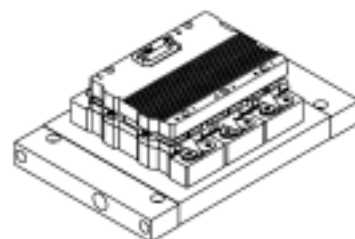
SKiiP® 3

SK integrated intelligent Power 2-pack

SKiiP 1803GB173-3DW

Preliminary data

Case S33



Features

- SKiiP technology inside
- Trench IGBTs
- CAL HD diode technology
- integrated current sensor
- integrated temperature sensor
- integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP® 3 System)
- IEC 68T.1 (climate) 40/125/56 (SKiiP® 3 power section)
- UL recognized File no. E63532 (SKiiP® 3 power section)

- 1) with assembly of suitable MKP capacitor per terminal (SEMİKRON type is recommended)
- 8) AC connection busbars must be connected by the user; copper busbars available on request

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SKiiP 1803GB173-3DW

SKiiP 3®

SK integrated intelligent Power

SKiiP 1803GB173-3DW

Preliminary data

Gate driver features

- CMOS compatible inputs
- wide range power supply
- integrated circuitry to sense phase current, heat sink temperature and DC-bus voltage (option)
- short circuit protection
- over current protection
- over voltage protection (option)
- power supply protected against under voltage
- interlock of top/bottom switch
- isolation by transformers
- fibre optic interface (option for GB-types only)
- IEC 68T.1 (climate) 40/85/56 (SKiiP® 3 gate driver)

II. Integrated gate driver

Absolute maximum ratings

Symbol	Term	Value	Unit
V _{S2}	unstabilized 24V power supply	30	V
V _{iH}	input signal voltage (high)	15 + 0,3	V
dv/dt	secondary to primary side	75	kV/μs
V _{isolIO}	input / output (AC, rms, 2 s)	4000	V
V _{isolPD}	partial discharge extinction voltage, rms, Q _{PD} ≤ 10 pC;	1500	V
V _{isol12}	output 1 / output 2 (AC, rms, 2s)	1500	V
f	switching frequency	9	kHz
T _{op} (T _{stg})	operating / storage temperature	- 40 ... + 85	°C

Electrical characteristics (T_a = 25 °C)

Symbol	Term	Values			Units
		min	typ	max.	
V _{S2}	supply voltage non stabilized	13	24	27	V
I _{S2}	V _{S2} = 24V	278 + 34*f / kHz + 0,00015 * (I _{AC} /A) ²			mA
V _{IT+}	input threshold voltage (High)	11,2	–	–	V
V _{IT-}	input threshold voltage (Low)	–	–	5,4	V
R _{in}	input resistance	–	10	–	kΩ
C _{in}	input capacitance	–	1	–	nF
t _{d(on)IO}	input-output turn-on propagation time	–	1,1	–	μs
t _{d(off)IO}	input-output turn-off propagation time	–	1,1	–	μs
t _{pERRRESET}	error memory reset time	–	9	–	μs
t _{TD}	top/bottom switch: interlock time	–	3,3	–	μs
I _{analogOUT}	max. 5mA ; 8 V corresponds to 15 V supply voltage for external components; max load current	–	1500	–	A
I _{S1out}		–	–	50	mA
I _{TRIPSC}	over current trip level (I _{analog OUT} = 10V)	–	1875	–	A
T _{tp}	over temperature protection	110	–	120	°C
U _{DCTRIPO}	U _{DC} -protection (U _{analog OUT} = 9V) (option for GB types)	not implemented	–	–	V

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